

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q78084

Hiromitsu SAKAI, et al.

Appln. No.: 10/575,625

Group Art Unit: 2811

Confirmation No.: 4644

Examiner: Shouxiang HU

Filed: April 13, 2006

For: GROUP-III NITRIDE SEMICONDUCTOR DEVICE

STATEMENT OF SUBSTANCE OF INTERVIEW

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Please review and enter the following remarks summarizing the interview conducted on January 11, 2011:

REMARKS

During the interview, the following was discussed:

1. Identification of claims discussed: 1-4, 6-14, and 16
2. Identification of art discussed: Shibata; Chang
3. Brief Identification of principal arguments:

Shibata only discloses the Al content of the second nitride $x_1=0.1$ which is twice the upper limit of 0.05 as set forth in claim 1. Accordingly, although Shibata discloses that the Al content of the second nitride is set smaller than the Al of the first nitride to reduce dislocation density, Shibata does not disclose an upper limit for the Al content 0.05 as claimed in claim 1 and does not provide any evidence supporting the reduction of the dislocation density when the Al content of the second nitride is further reduced.

Further, claim 1 recites the third nitride semiconductor layer having the Al content $x_2 \leq 0.5$, which is substantially less than the Al content of 0.95 as employed in the working examples of Shibata.

4. Results of Interview: No agreement was reached

It is respectfully submitted that the instant STATEMENT OF SUBSTANCE OF INTERVIEW complies with the requirements of 37 C.F.R. §§1.2 and 1.133 and MPEP §713.04.

It is believed that no petition or fee is required. However, if the USPTO deems otherwise, Applicant hereby petitions for any extension of time which may be required to maintain the pendency of this case, and any required fee, except for the Issue Fee, for such extension is to be charged to Deposit Account No. 19-4880.

Respectfully submitted,

/ Marina V. Zalevsky /

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WASHINGTON OFFICE

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CUSTOMER NUMBER

Date: February 10, 2011

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